

MITSUBISHI IGBT MODULES
CM1000DUC-34NF
 HIGH POWER SWITCHING USE
 INSULATED TYPE

CM1000DUC-34NF

- MPD series using 5th Generation IGBT and FWDi -



Dual (Half-Bridge)

- I_C 1000 A
- V_{CES} 1700 V
- Flat base Type
Copper (non-plating) base plate
- RoHS Directive compliant

APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm

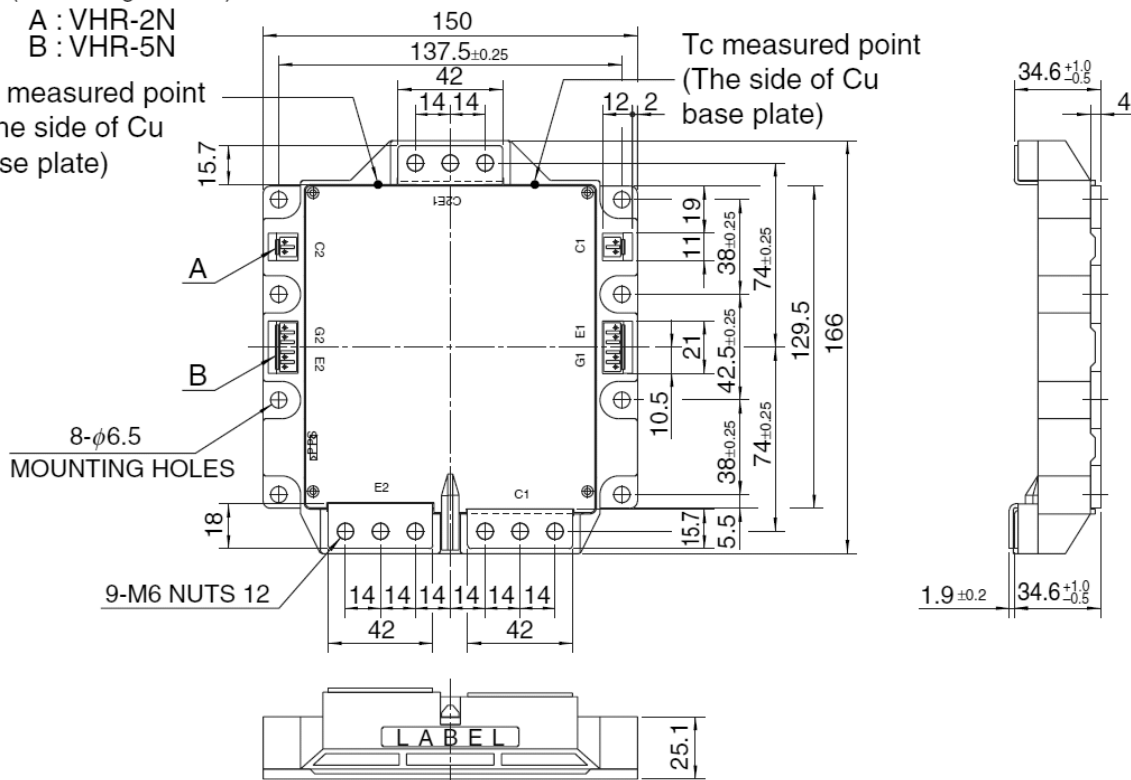
A,B HOUSING Type

(J. S. T. Mfg. Co. Ltd)

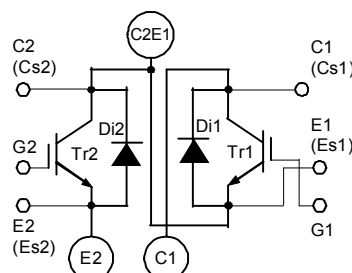
A : VHR-2N

B : VHR-5N

Tc measured point
(The side of Cu
base plate)



INTERNAL CONNECTION



Tolerance otherwise specified	
Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

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ABSOLUTE MAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=104\text{ }^\circ\text{C}$ (Note.2)	1000	A
I_{CRM}		Pulse, Repetitive (Note.3)	2000	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	8925	W
I_E (Note.1)	Emitter current	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	1000	A
I_{ERM} (Note.1)	(Free wheeling diode forward current)	Pulse, Repetitive (Note.3)	2000	
T_j	Junction temperature	-	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	(Note.7)	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	3500	V

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1	mA	
I_{GES}	Gate-emitter leakage current	$\pm V_{GE}=V_{GES}$, C-E short-circuited	-	-	5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=100\text{ mA}$, $V_{CE}=10\text{ V}$	6	7	8	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1000\text{ A}$ (Note.5), $V_{GE}=15\text{ V}$	$T_j=25\text{ }^\circ\text{C}$	-	2.2	2.85	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.45	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	220	nF	
C_{oes}	Output capacitance		-	-	25		
C_{res}	Reverse transfer capacitance		-	-	4.7		
Q_G	Gate charge	$V_{CC}=1000\text{ V}$, $I_C=1000\text{ A}$, $V_{GE}=15\text{ V}$	-	6000	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=1000\text{ V}$, $I_C=1000\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, Inductive load	-	-	600	ns	
t_r	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	1000		
t_f	Fall time		-	-	300		
V_{EC} (Note.1)	Emitter-collector voltage	$I_E=1000\text{ A}$ (Note.5), G-E short-circuited	-	2.3	3.0	V	
t_{rr} (Note.1)	Reverse recovery time	$V_{CC}=1000\text{ V}$, $I_E=1000\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, Inductive load	-	-	500	ns	
Q_{rr} (Note.1)	Reverse recovery charge	$R_G=0.47\text{ }\Omega$, Inductive load	-	90	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=1000\text{ V}$, $I_C=I_E=1000\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\text{ }\Omega$, $T_j=125\text{ }^\circ\text{C}$, Inductive load	-	272.4	-	mJ	
E_{off}	Turn-off switching energy per pulse		-	250.2	-		
E_{rr} (Note.1)	Reverse recovery energy per pulse		-	172.4	-		
R_{CC+EE}	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note.2)	-	0.286	-	m Ω	
r_g	Internal gate resistance	Per switch	-	0.67	-	Ω	

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance (Note.2)	Junction to case, per IGBT	-	-	14	K/kW
$R_{th(j-c)D}$		Junction to case, per FWDi	-	-	23	
$R_{th(c-s)}$	Contact thermal resistance (Note.2)	Case to heat sink, per 1/2 module, Thermal grease applied (Note.6)	-	12	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M_s		Mounting to heat sink M 6 screw	3.5	4.0	4.5	
m	Weight	-	-	1450	-	g
e_c	Flatness of base plate	On the centerline X, Y1, Y2 (Note.8)	-50	-	+100	μm

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RECOMMENDED OPERATING CONDITIONS ($T_a=25\text{ }^\circ\text{C}$)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2	-	1000	1100	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	
R_G	External gate resistance	Per switch	0.47	-	4.7	Ω

Note.1: Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).

Note.2: Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface of base plate and heat sink just under the chips. (Refer to the figure of chip location)

The heat sink thermal resistance $\{R_{th(s-a)}\}$ should measure just under the chips.

Note.3: Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.

Note.4: Junction temperature (T_j) should not increase beyond T_{jmax} rating.

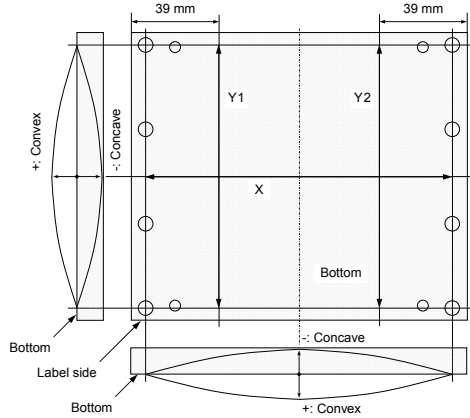
Note.5: Pulse width and repetition rate should be such as to cause negligible temperature rise.

(Refer to the figure of test circuit)

Note.6: Typical value is measured by using thermally conductive grease of $\lambda=0.9\text{ W/(m}\cdot\text{K)}$.

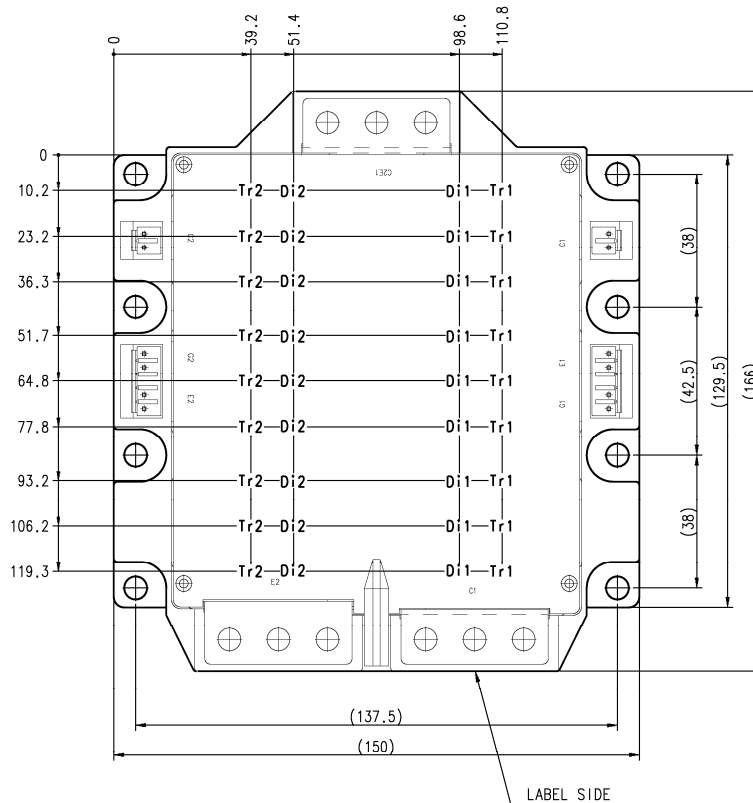
Note.7: The operation temperature is restrained by the permission temperature of female connector housing.

Note.8: Base plate flatness measurement points are as in the following figure.



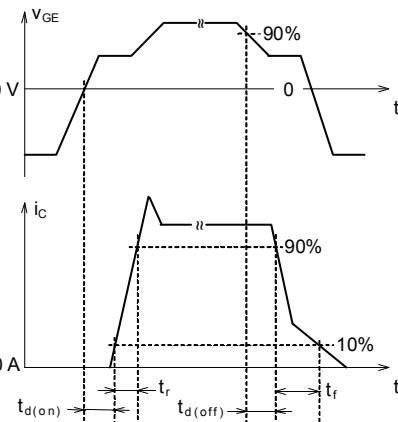
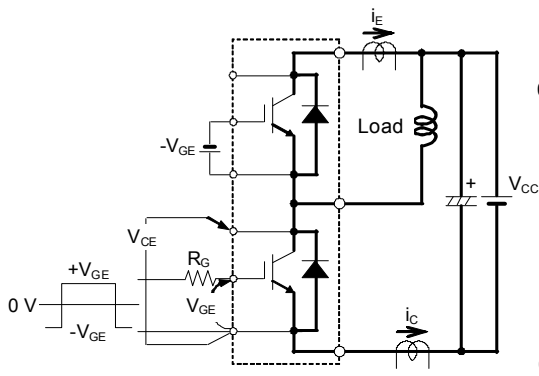
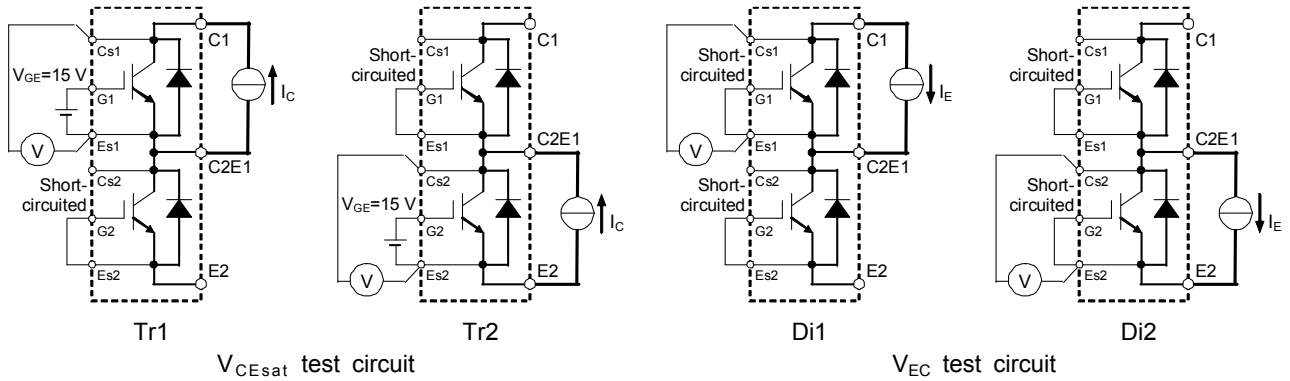
CHIP LOCATION (Top view)

Dimension in mm, tolerance: $\pm 1\text{ mm}$



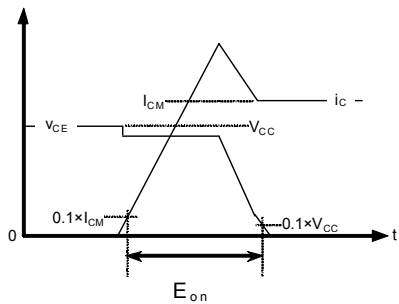
Tr1/Tr2: IGBT, Di1/Di2: FWDi. Each mark points the center position of each chip.

TEST CIRCUIT AND WAVEFORMS

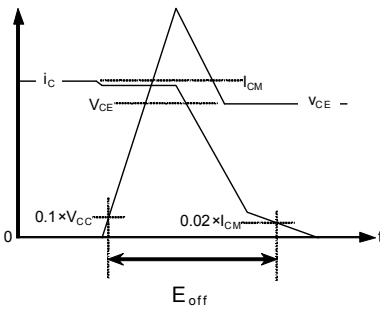


Switching characteristics test circuit and waveforms

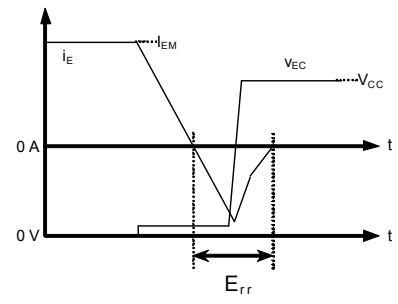
t_{rr} , Q_{rr} test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy

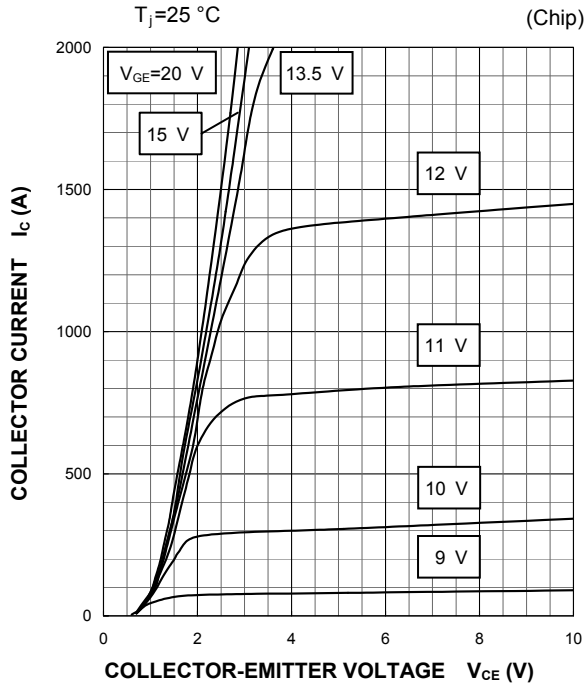


FWDi Reverse recovery energy

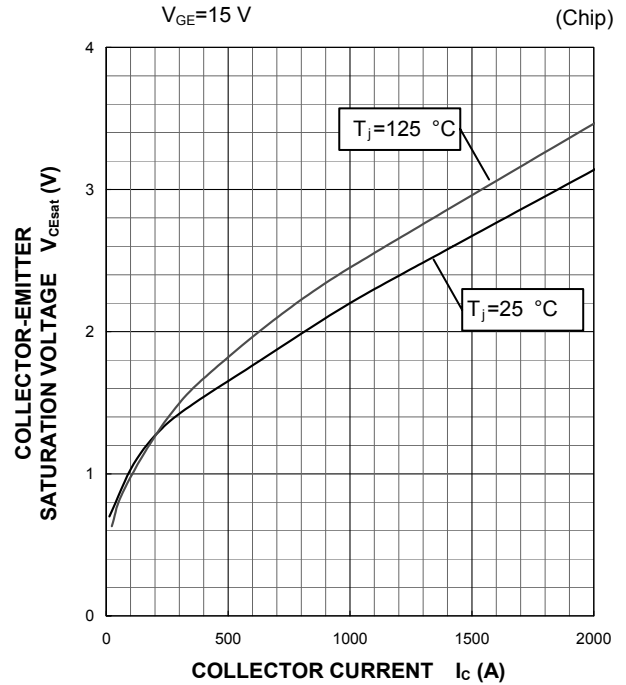
Turn-on / Turn-off switching energy and Reverse recovery energy integral range

PERFORMANCE CURVES

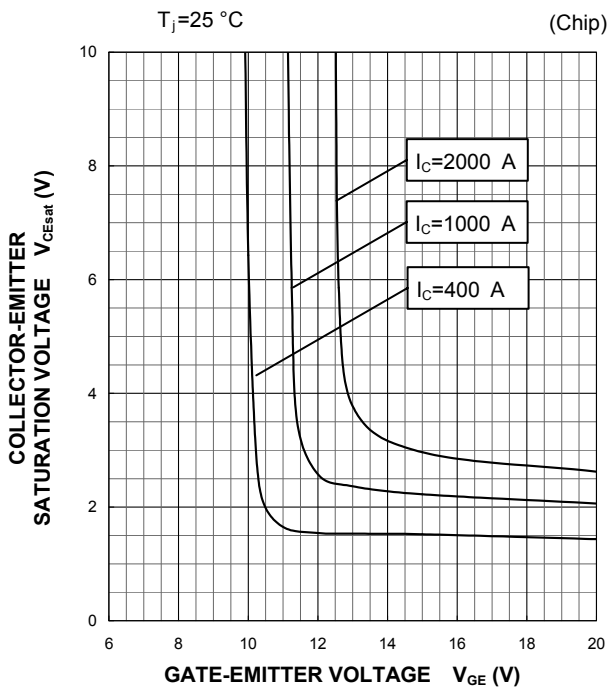
OUTPUT CHARACTERISTICS
 (TYPICAL)



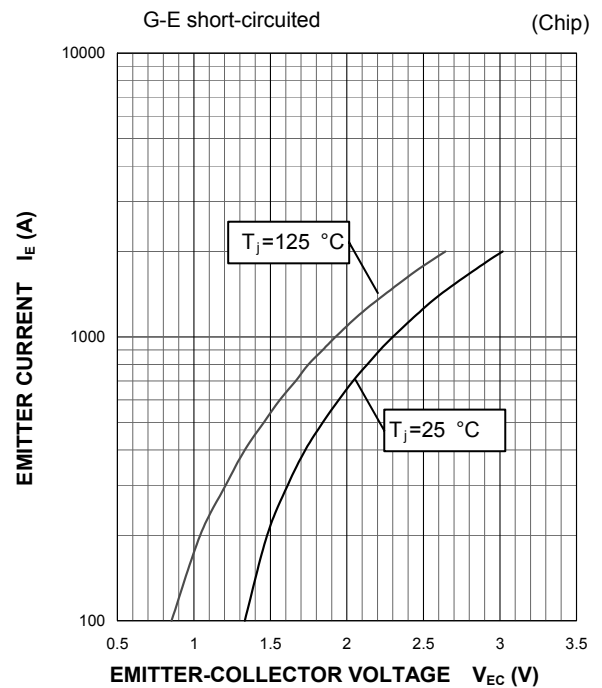
COLLECTOR-EMITTER SATURATION
 VOLTAGE CHARACTERISTICS
 (TYPICAL)



COLLECTOR-EMITTER SATURATION
 VOLTAGE CHARACTERISTICS
 (TYPICAL)



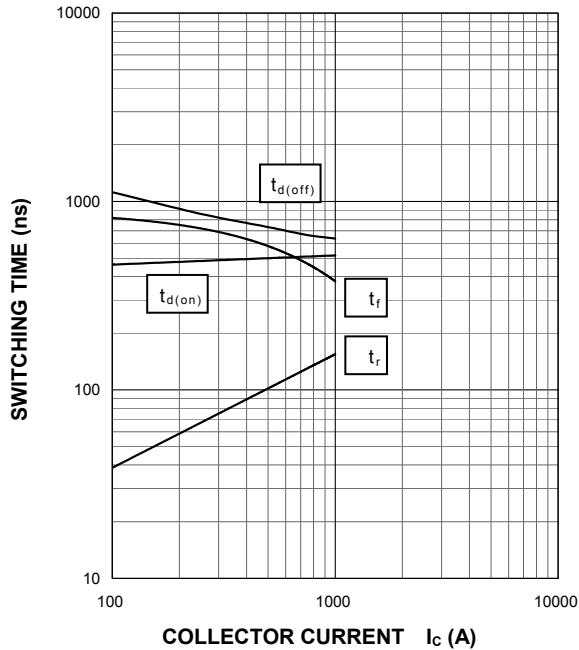
FREE WHEELING DIODE
 FORWARD CHARACTERISTICS
 (TYPICAL)



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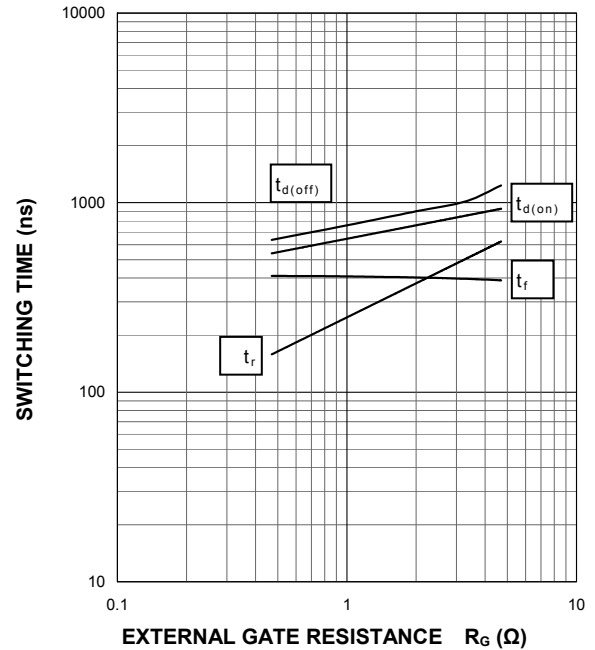
HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\ \Omega$, $T_j=125\text{ }^\circ\text{C}$,
 INDUCTIVE LOAD



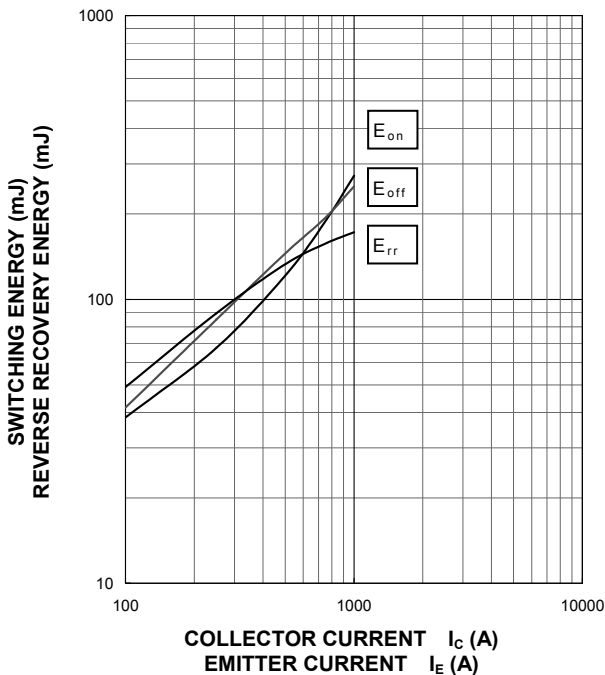
HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)

$V_{CC}=1000\text{ V}$, $I_C=1000\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $T_j=125\text{ }^\circ\text{C}$,
 INDUCTIVE LOAD



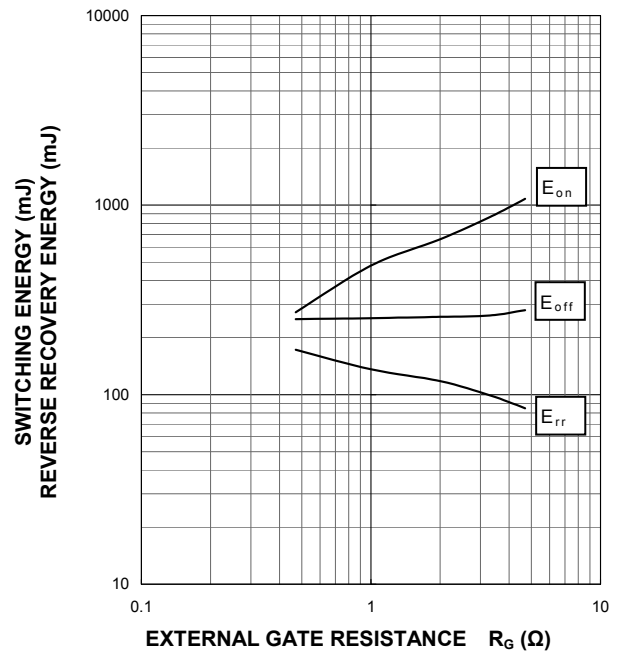
HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\ \Omega$, $T_j=125\text{ }^\circ\text{C}$,
 INDUCTIVE LOAD, PER PULSE



HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)

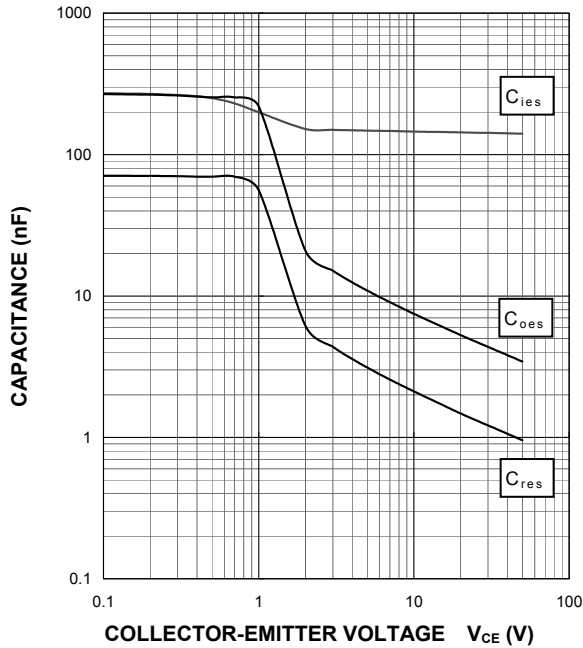
$V_{CC}=1000\text{ V}$, $I_C/I_E=1000\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $T_j=125\text{ }^\circ\text{C}$,
 INDUCTIVE LOAD, PER PULSE



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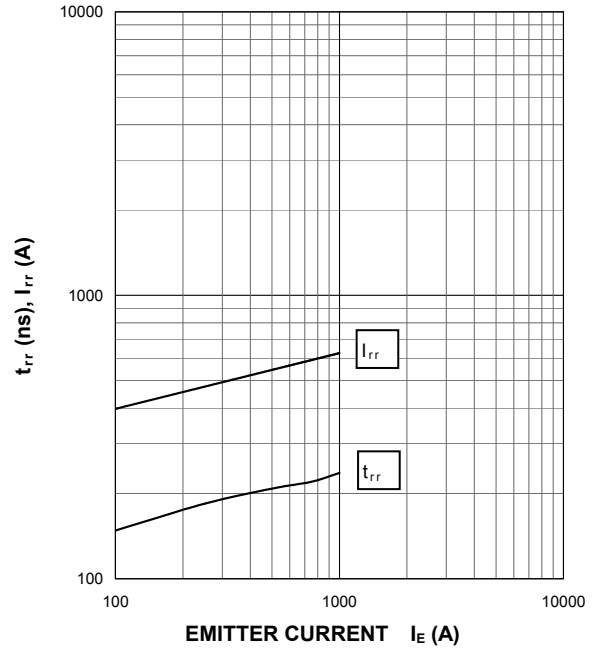
**CAPACITANCE CHARACTERISTICS
 (TYPICAL)**

G-E short-circuited, $T_j=25\text{ }^\circ\text{C}$



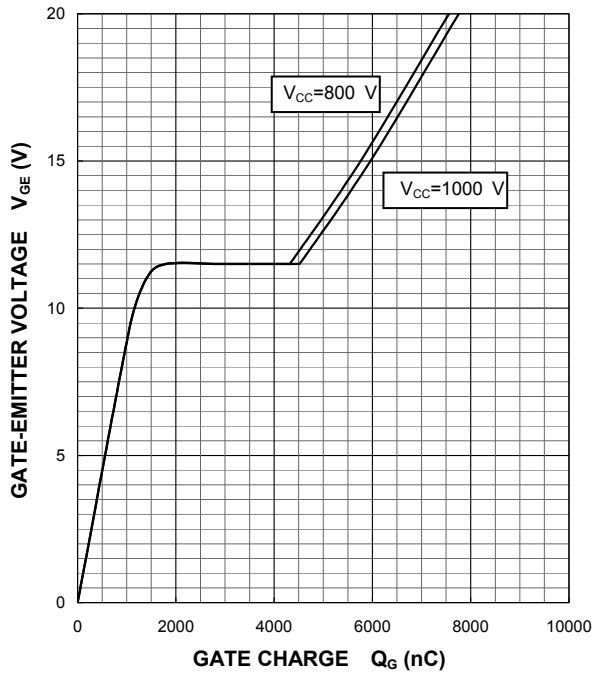
**FREE WHEELING DIODE
 REVERSE RECOVERY CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=1000\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.47\ \Omega$, $T_j=25\text{ }^\circ\text{C}$,
 INDUCTIVE LOAD



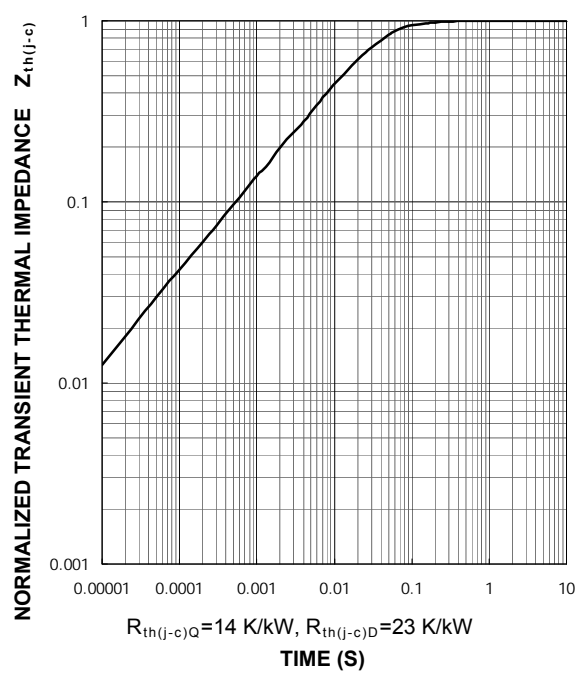
**GATE CHARGE CHARACTERISTICS
 (TYPICAL)**

$I_c=1000\text{ A}$, $T_j=25\text{ }^\circ\text{C}$



**TRANSIENT THERMAL IMPEDANCE
 CHARACTERISTICS
 (MAXIMUM)**

Single pulse, $T_c=25\text{ }^\circ\text{C}$



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